

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. *(Original)* A device manufacturing method comprising:
providing a substrate;
providing a first layer of electromagnetic radiation sensitive material on said substrate;
providing a second layer of electromagnetic radiation sensitive material on said first layer of radiation sensitive material, said second layer of radiation sensitive material being of a different material than said first layer of radiation sensitive material;
providing a beam of electromagnetic radiation using an illumination system;
imparting said beam of radiation with a desired pattern in its cross-section by employing a patterning device; and
projecting said patterned beam of radiation onto a target portion of said first and second layers of radiation sensitive material.
2. *(Original)* The device manufacturing method of Claim 1, wherein said first layer of radiation sensitive material has a dose size of approximately 1.5 times to 2.5 times the magnitude of the dose size of said second layer of radiation sensitive material.
3. *(Original)* The device manufacturing method of Claim 1, wherein said first layer is thinner than said second layer.
4. *(Original)* The device manufacturing method of Claim 1, wherein said first layer is between 100 and 500nm thick and said second layer is between 500 and 1500 nm thick.
5. *(Original)* The device manufacturing method of Claim 1, wherein said first and second materials are substantially immiscible.

6. *(Original)* The device manufacturing method of Claim 1, wherein said first and second materials are based on a similar generic solvent.

7. *(Original)* The device manufacturing method of Claim 1, wherein said first and second materials are based on bulky-acetal polymers.

8. *(Original)* The device manufacturing method of Claim 7, wherein said first and second materials have different solvents.

9. *(Original)* The device manufacturing method of Claim 1, wherein said first layer material comprises GKRS 6202 and said second layer material comprises ARCH 8250.

10. *(Original)* The device manufacturing method of Claim 1, wherein said first and second layer materials are positively radiation sensitive.

11. *(Original)* The device manufacturing method of Claim 1, further comprising developing said first and second layers of radiation sensitive material to remove portions which have been exposed.

12. *(Original)* The device manufacturing method of Claim 11, wherein said removed portion of said first layer is smaller than said removed portion of said second layer.

13. *(Original)* The device manufacturing method of Claim 11, wherein said second layer overhangs said first layer after developing.

14. *(Original)* The device manufacturing method of Claim 11, further comprising depositing a first layer of metal onto said substrate.

15. *(Original)* The device manufacturing method of Claim 14, further comprising lifting off said first and second layers of radiation sensitive material to leave a T-gate on said substrate.

16. *(Original)* The device manufacturing method of Claim 14, further comprising, before said lifting off, depositing a second layer of metal onto said substrate.

17. *(Original)* The device manufacturing method of Claim 16, wherein said first layer of metal comprises Ti or Pt and said second layer comprises Pt or Au.

18. *(Original)* The device manufacturing method of Claim 16, further comprising depositing a third layer of metal onto said substrate.

19. *(Original)* The device manufacturing method of Claim 18, wherein said third layer of metal comprises Au.

20. *(Currently Amended)* A substrate for use in an electromagnetic lithographic apparatus, said substrate comprising:

a first layer of electromagnetic radiation sensitive material attached to a surface;
and

a second layer of electromagnetic radiation sensitive material attached to said first layer of radiation sensitive material,

wherein said first layer of radiation sensitive material is of a different material ~~to~~ than said second layer of radiation sensitive material and said first layer of radiation sensitive material has a dose size of at least approximately 1.5 times the magnitude of the dose size of said second layer of radiation sensitive material.

21. *(Original)* The substrate of Claim 20, wherein said first layer of radiation sensitive material has a dose size of approximately 1.5 times to 2.5 times the magnitude of the dose size of said second layer of radiation sensitive material.

22. (*Original*) The substrate of Claim 20, wherein said first and second materials are based on similar generic solvents.

23. (*New*) The device manufacturing method of Claim 1, wherein said substrate comprises GaAs, Si, GaN, InP, or SiGa.

24. (*New*) The device manufacturing method of Claim 1, wherein said method is a process for the manufacture of an integrated circuit having a T-gate.

25. (*New*) The substrate of Claim 20, wherein said substrate comprises GaAs, Si, GaN, InP, or SiGa.